

L-Band, GaN/SiC, RF Power Transistor

1.03 & 1.09 GHz | 400W typ | 68% Efficiency typ | 20.5 dB Gain typ | 50 V | 32μs Pulse Length, 4% Duty Cycle

IGN1011S350 and IGN1011S350S are high power GaN-on-SiC RF power transistors that have been designed to suit the unique needs of IFF and avionic systems. They operate at both 1030 and 1090 MHz. Under 32μs, 4% duty cycle pulse conditions, they supply a minimum of 350 W of peak output power. They operate from a 50 V supply voltage. For optimal thermal efficiency, the transistors are housed in a metal-based package with an epoxy-sealed ceramic lid.

FEATURES

- GaN on SiC HEMT Technology
- Output Power >350W
- Pre-matched Input Impedance
- High Efficiency - up to 68%
- 100% RF Tested Under 32μs, 4% duty cycle pulse conditions
- RoHS and REACH Compliant

APPLICATIONS

- IFF and SSR Avionic Systems

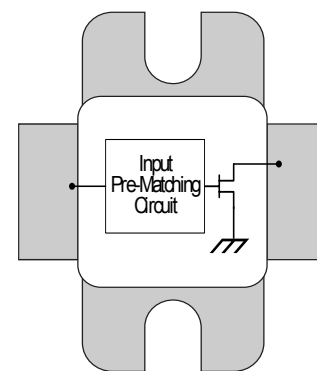


Table 1. Absolute Maximum Ratings (Not Simultaneous)

| Parameter | Symbol | Value | Units | Test Conditions |
|-------------------------------|--------------|-------------|-------|-----------------|
| DC Drain-Source Voltage | V_{DS} | 150 | V | 25 °C |
| DC Gate-Source Voltage | V_{GS} | -8 to +1.0 | V | 25 °C |
| DC Drain Current | I_D | 54 | A | 25 °C |
| DC Gate Current | I_G | 5.4 | mA | 25 °C |
| RF Input Power | $P_{RF,IN}$ | 40 | W | 25 °C |
| Operating Channel Temperature | T_J | -55 to +225 | °C | |
| Storage Temperature | T_{STG} | -62 to +150 | °C | |
| Soldering Temperature | T_{SOLDER} | 260 for 60s | °C | |

Note: Operation outside the limits given in this table may cause permanent damage to the transistor

Table 2. DC Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

| Parameter | Symbol | Min | Typ | Max | Units | Test Conditions |
|------------------------|--------|------|------|-----|-------|-------------------------------|
| Gate Pinch-Off Voltage | V_P | -5.0 | | | V | $V_{DS} = 50V, I_{DS} = 1mA$ |
| Quiescent Gate Voltage | V_Q | | -2.8 | | V | $V_{DS} = 50V, I_{DS} = 50mA$ |

Table 3. RF Electrical Characteristics in Standard Test Fixture (Case temperature = 30 °C unless otherwise stated)

| Parameter | Symbol | Min | Typ | Max | Units | Test Conditions |
|-------------------------|----------|------|------|-----|-------|--|
| Gain | G | 17 | 18.5 | 20 | dB | $P_{OUT} = 350W$ $f = 1.03, 1.09GHz$ 32 μs pulse length, 4% duty cycle $V_{DS} = 50V, I_{DS} = 50mA$ |
| Drain Efficiency | η | 55 | 63 | 70 | % | |
| Pulse Droop | D | -0.4 | -0.1 | 0.2 | dB | |
| Load Mismatch Stability | VSWR-S | | 2:1 | | | |
| VSWR Withstand | VSWR-LMT | | 5:1 | | | |

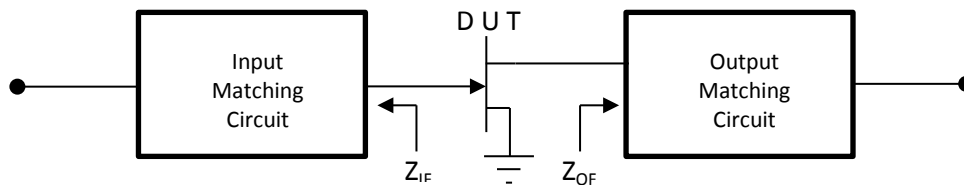
Note: Consult Integra Technologies Application Note 001 for information on how RF output power and pulse droop are measured.

Table 4. Thermal Resistance (Case temperature = 85 °C unless otherwise stated)

| Parameter | Symbol | Typ | Test Conditions |
|--|----------|-----|---|
| Peak Thermal Resistance, Channel to Case | R_{TH} | 0.3 | $P_{DISS} = 206W$ 32 μs pulse length, 4% duty cycle $V_{DS} = 50V$ |

Table 5. Standard Test Fixture Source & Load Impedances (Case temperature = 25 °C unless otherwise stated)

| Frequency (GHz) | Z_{IF} | Z_{OF} Fundamental | Units | Test Conditions |
|-----------------|-------------|----------------------|----------|---|
| 1.03 | 2.7 - j 2.4 | 2.1 + j 0.2 | Ω | $P_{OUT} = 350W$ 32 μs pulse length, 4% duty cycle $V_{DS} = 50V, I_{DS} = 50mA$ |
| 1.09 | 2.7 - j 1.9 | 2.3 + j 0.6 | Ω | |



TYPICAL PERFORMANCE IN STANDARD TEST FIXTURE

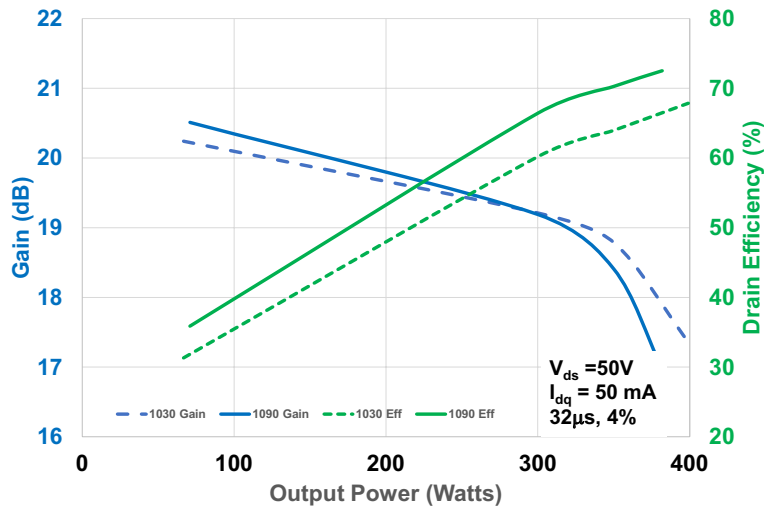


Figure 1

TYPICAL PERFORMANCE IN MINIATURIZED TEST FIXTURE

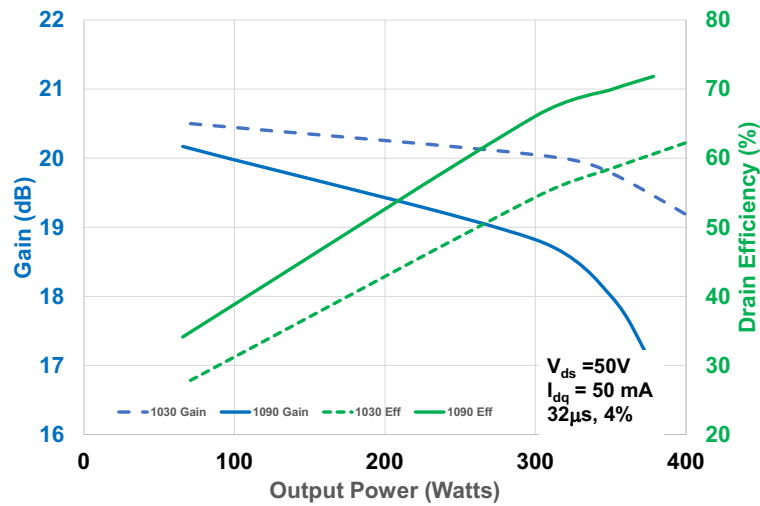
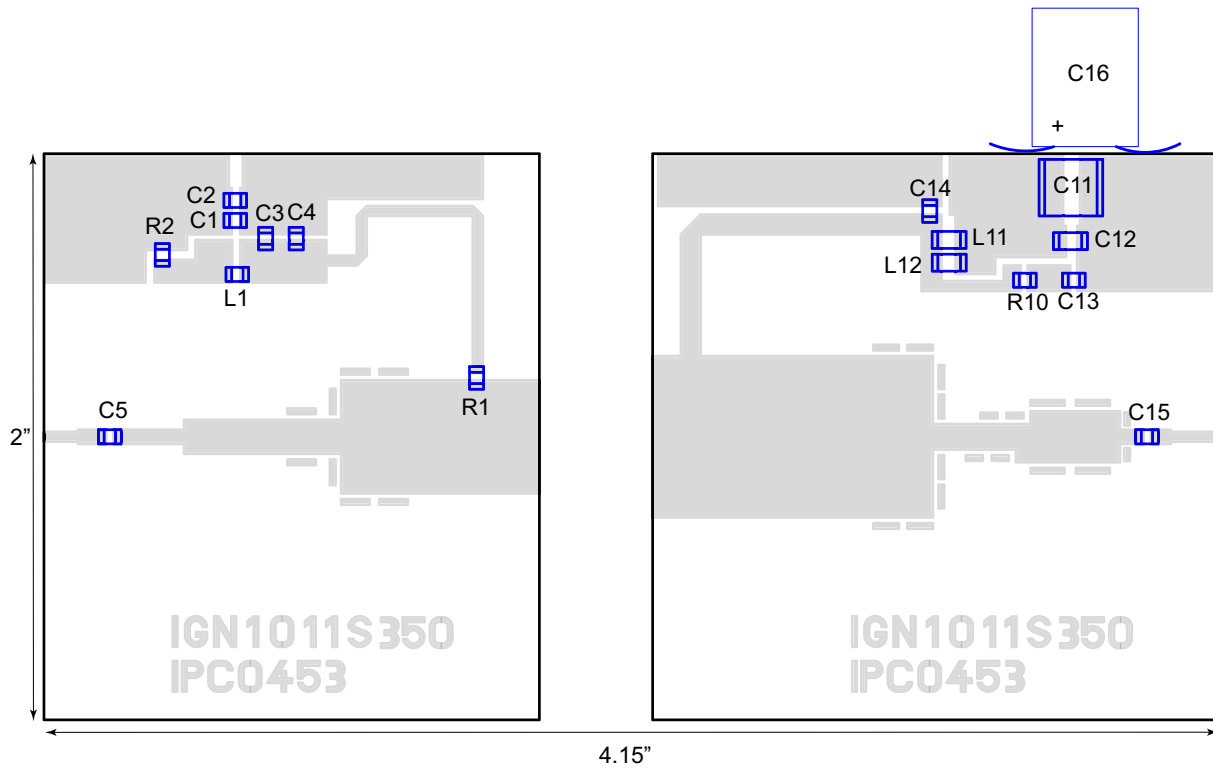


Figure 2

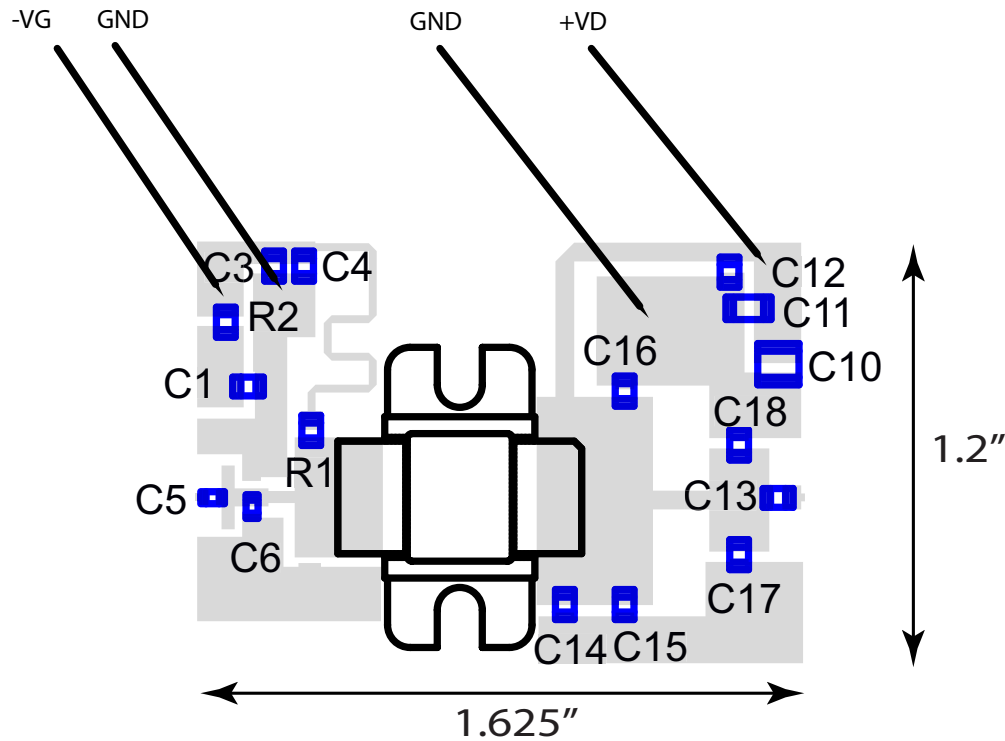
STANDARD TEST FIXTURE



Bill of Materials for IGN1011S350 Standard Test Fixture

| Designator | Description | Part Number |
|---------------|------------------------------------|-----------------|
| C1, C13 | CAP 0.01 μ F, 0805, 50V | 0805C103K4Z2A |
| C2, C4 | CAP 18pF, 0805, 50V | ATC600F180 |
| C3 | CAP 1000pF, 0805, 50V, X7R | 0805C102K5RACTU |
| C5, C6, C15 | CAP 18pF, 0805, Edge Mount | ATC600F180 |
| C11 | CAP 10 μ F, 2220, 100V, X7R | 22201C106MAT2A |
| C12 | CAP 1 μ F, 1206 | 12061C105KAT2A |
| C14 | CAP 100pF | ATC600F102 |
| C16 | CAP 68 μ F, 63V, Electrolytic | UPJ1J680MPD |
| L1 | IND FB, 120 OHM, 0805, 5A | ILHB0805ER121V |
| L11, L12 | IND FB 33 OHM, 1206, 6A | BLM31PG330SH1L |
| R1, R10 | RES 10 OHM, 0805, 0.1W | ERJ-2GEJ100X |
| R2 | RES 100 OHM, 0805, 0.1W | ERJ-2RKF1000X |
| PC Board Type | ROGERS RT6006 25mil, 1/1oz. Copper | |

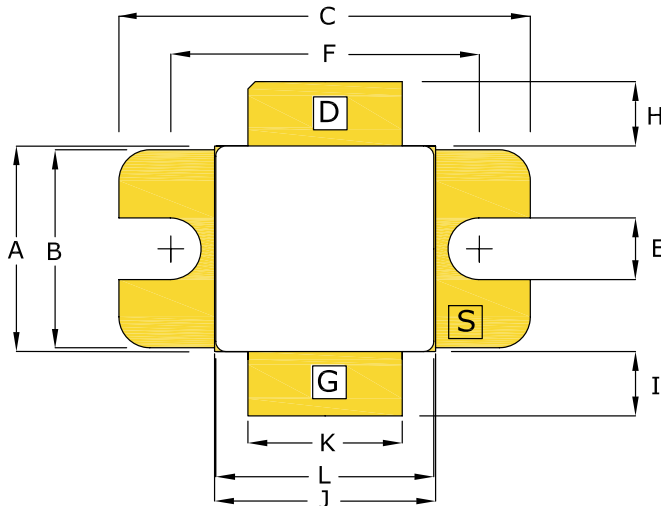
MINIATURIZED TEST FIXTURE



Bill of Materials for Miniaturized Test Fixture

| Designator | Description | Part Number |
|---------------|------------------------------------|------------------|
| C1 | CAP 0.01 μ F, 0805, 100V | 0805C103K4Z2A |
| C3 | CAP 1000pF, 0805, 50V, X7R | C0805C102K5RACTU |
| C4 | CAP 10pF, 0805, 250V | ATC600F100 |
| C5 | CAP 10pF, 0603, 250V | ATC600S100 |
| C6 | CAP 6.3PF, 0805, 250V | ATC600S6R3 |
| C10 | CAP 100pF, 2220, 100V, X7R | ATC100B102 |
| C11 | CAP 1 μ F, 1206, 100V | 12061C105KAT2A |
| C12 | CAP 100pF, 0805, 100V | ATC600F102 |
| C13 | CAP 18pF, 0805, 100V | ATC600F180 |
| C14 | CAP 2.7pF, 0805, 100V | ATC600F2R7 |
| C15 | CAP 5.6pF, 0805, 100V | ATC600F5R6 |
| C16 | CAP 4.7pF, 0805, 100V | ATC600F4R7 |
| C17 | CAP 3.3pF, 0805, 100V | ATC600F3R3 |
| C18 | CAP 1.2pF, 0805, 100V | ATC600F1R2 |
| C19 | CAP 68 μ F, 63V, Electrolytic | UPJ1J680MPD |
| L1 | IND FB, 120 OHM, 0805, 5A | ILHB0805ER121V |
| R1 | RES 10 OHM, 0805, 0.1W | ERJ-6ENF10R0V |
| R2 | RES 100 OHM, 0805, 0.1W | ERJ-6ENF1000V |
| PC Board Type | ROGERS RO3010 25mil, 1/1oz. Copper | |

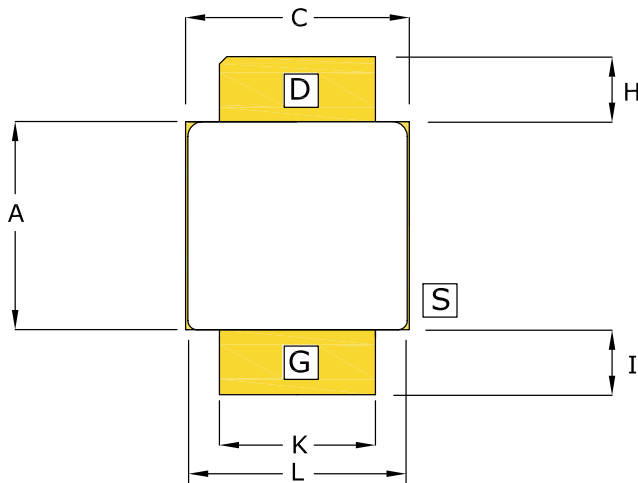
PACKAGE PL44C1 FLANGED AND EARLESS VERSIONS



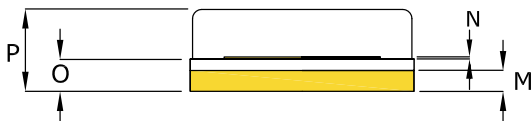
| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.395 | 0.405 | 10.03 | 10.29 |
| B | 0.380 | 0.390 | 9.65 | 9.91 |
| C | 0.795 | 0.805 | 20.19 | 20.45 |
| E | 0.115 | 0.125 | 2.92 | 3.18 |
| F | 0.595 | 0.605 | 15.11 | 15.37 |
| H | 0.110 | 0.140 | 2.79 | 3.56 |
| I | 0.110 | 0.140 | 2.79 | 3.56 |
| J | 0.425 | 0.435 | 10.80 | 11.05 |
| K | 0.295 | 0.305 | 7.49 | 7.75 |
| L | 0.420 | 0.428 | 10.67 | 10.87 |
| M | 0.035 | 0.045 | 0.89 | 1.14 |
| N | 0.004 | 0.007 | 0.10 | 0.18 |
| O | 0.053 | 0.067 | 1.35 | 1.70 |
| P | 0.143 | 0.179 | 3.63 | 4.55 |



| PIN SCHEDULE | |
|--------------|--------|
| D | DRAIN |
| S | SOURCE |
| G | GATE |



| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.393 | 0.408 | 9.97 | 10.35 |
| B | -- | -- | -- | -- |
| C | 0.423 | 0.438 | 10.73 | 11.11 |
| E | -- | -- | -- | -- |
| F | -- | -- | -- | -- |
| H | 0.110 | 0.140 | 2.79 | 3.56 |
| I | 0.110 | 0.140 | 2.79 | 3.56 |
| J | -- | -- | -- | -- |
| K | 0.295 | 0.305 | 7.49 | 7.75 |
| L | 0.420 | 0.428 | 10.67 | 10.87 |
| M | 0.035 | 0.045 | 0.89 | 1.14 |
| N | 0.004 | 0.007 | 0.10 | 0.18 |
| O | 0.053 | 0.067 | 1.35 | 1.70 |
| P | 0.143 | 0.179 | 3.63 | 4.55 |



| PIN SCHEDULE | |
|--------------|--------|
| D | DRAIN |
| S | SOURCE |
| G | GATE |

ESD & MSL Rating

| Parameter | Rating | Standard |
|----------------------------------|----------------------|------------------------|
| ESD Human Body Model (HBM) | TBD | ESDA/JEDEC JS-001-2012 |
| ESD Charged Device Model (CDM) | TBD | JEDEC JESD22-C101F |
| Moisture Sensitivity Level (MSL) | Unlimited Shelf Life | IPC/JEDEC J-STD-020 |

RoHS Compliance

Integra Technologies, Inc declares that its GaN and LDMOS Transistor Products comply with EU Directive 2011/65/EU on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863/EU.

REACH Compliance

Integra Technologies supports EU Regulation number 1907/2006 concerning the Registration, Evaluation, Authorization, and Restriction of Chemicals (REACH) as these apply to Integra semiconductor products, development tools, and shipping packaging.

In support of the REACH regulation, Integra will:

- Inform customers and recipients of Integra product if they contain any substances that are of very high concern (SVHC) per the European Chemical Agency (ECHA) website.
- Notify ECHA if any Integra product that contains any SVHCs which exceed guidelines for REACH chemicals by weight per part number and for total content weight per year for all products produced in or imported to the European market.
- Cease shipments of product containing REACH Annex XIV substances until authorization has been obtained.
- Cease shipment of product containing REACH Annex XVII chemicals when restrictions apply.

Integra has evaluated its materials, BOMs, and product specifications and product and has determined that this transistor conforms to all REACH and SVHC regulations and guidelines. Integra has implemented actions and control programs that will assure continued compliance.

Disclaimer

Integra Technologies Inc. reserves the right to make changes without further notice to any products herein. Integra Technologies Inc. makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Integra Technologies Inc. assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. Integra Technologies Inc. products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Integra Technologies Inc. customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Integra Technologies Inc. for any damages resulting from such improper use or sale.

DEFINITIONS:

DATA SHEET STATUS

Advanced Specification - This data sheet contains Advanced specifications.

Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.

Final Specification - This data sheet contains final product specifications.

MAXIMUM RATINGS Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.

Integra Technologies, 321 Coral Circle, El Segundo, CA 90245-4620 | Phone: 310-606-0855 | Fax: 310-606-0865